

Supplementary Information

Interfacial engineering with Carbon-Graphite- $\text{Cu}_\delta\text{Ni}_{1-\delta}\text{O}$ composites for ambient-air stable hole-conductor-free perovskite solar cells

Yousheng Wang*, Yuzhao Yang, Shaohang Wu, Cuiling Zhang, Zhen Wang, Jinlong Hu, Chong Liu, Fei Guo and Yaohua Mai*

Institute of New Energy Technology, College of Information Science and Technology, Jinan University, Guangzhou 510632, China

*E-mail address: wangys0120@jnu.edu.cn;

*E-mail address: yaohuamai@jnu.edu.cn;

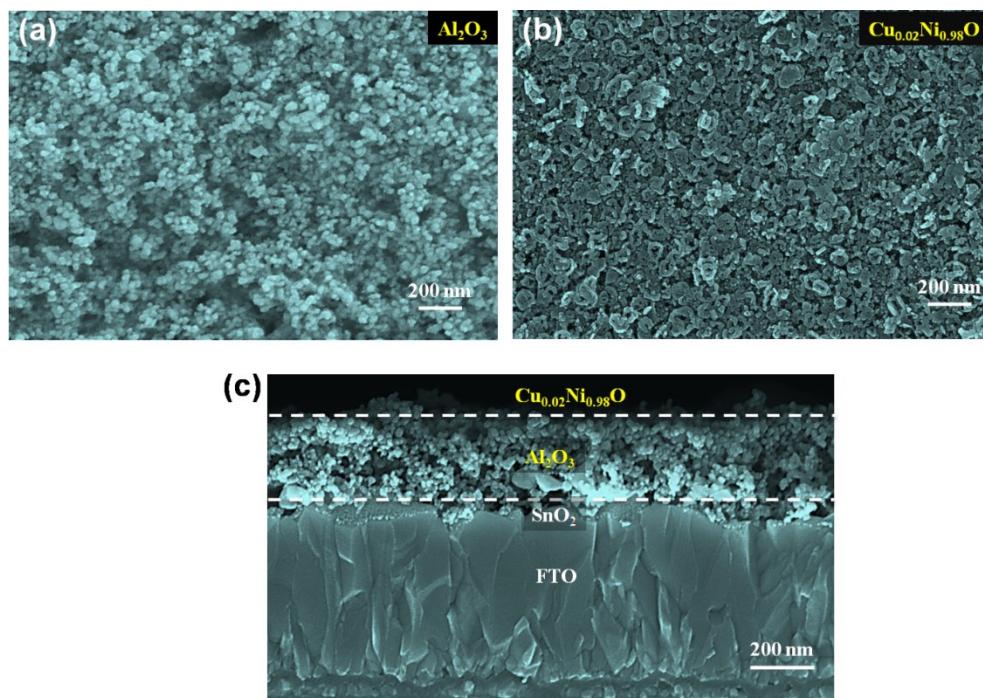


Figure S1 (a) The surface morphology of Al_2O_3 and (b) as-synthesized $\text{Cu}_{0.02}\text{Ni}_{0.98}\text{O}$ thin film and (c) cross-sectional SEM image of FTO/ SnO_2 / Al_2O_3 / $\text{Cu}_{0.02}\text{Ni}_{0.98}\text{O}$.

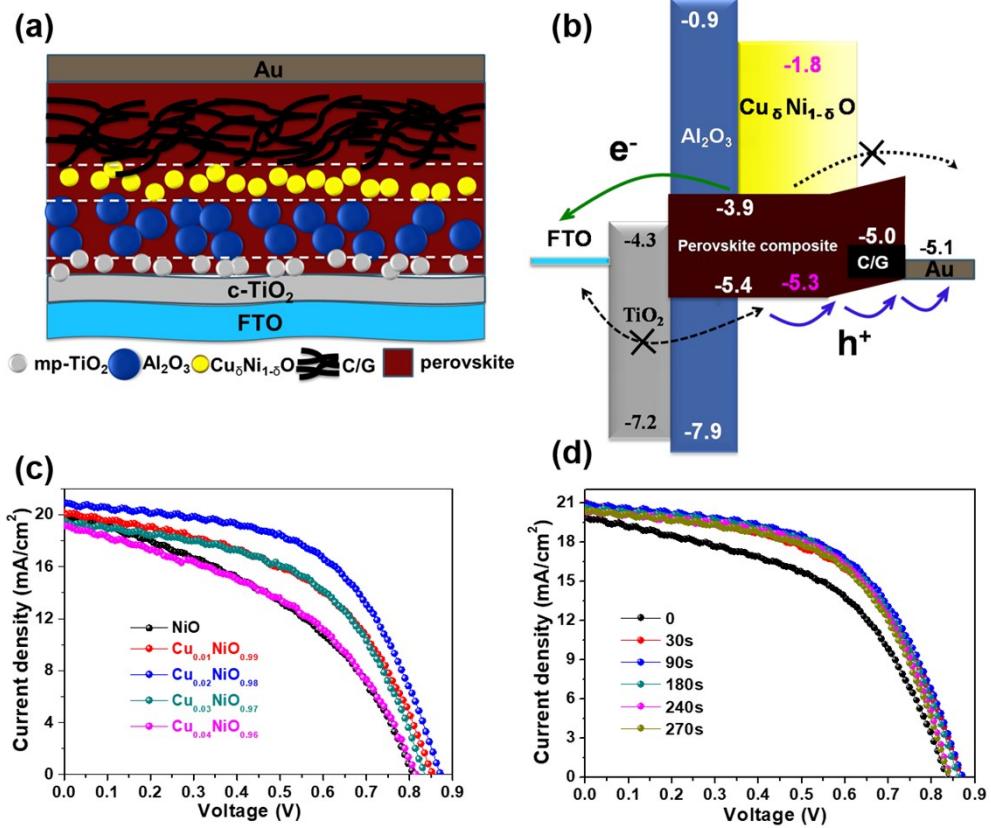


Figure S2 (a) Schematic of device configuration of FTO/c-TiO₂/mp-TiO₂/Al₂O₃/Cu_δNi_{1-δ}O/C-G/MAPbI_{3-x}Cl_x/Au and (b) corresponding the band energy diagram; (c) *J-V* performance for different Cu doping contents of Cu_δNi_{1-δ}O films; (d) continuous 1-sun illumination effect of carbon based HCF device of Cu_{0.02}Ni_{0.98}O.

Table S1 Photovoltaic parameters (Figure S2c) of carbon based HCF-PSCs FTO/c-TiO₂/mp-TiO₂/Al₂O₃/Cu_δNi_{1-δ}O/C-G/MAPbI_{3-x}Cl_x/Au for different Cu doping contents of Cu_δNi_{1-δ}O films.

δ (Cu _δ Ni _{1-δ} O)	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
0	0.82	20.25	41.66	6.92
0.01	0.86	20.28	49.28	8.60
0.02	0.88	20.97	55.30	10.21
0.03	0.84	19.55	52.35	8.60
0.04	0.83	19.13	44.21	7.02

Table S2 Photovoltaic parameters (Figure S2d) for continuous 1-sun illumination effect of carbon based HCF device FTO/c-TiO₂/mp-TiO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G/MAPbI_{3-x}Cl_x/Au.

Photo-stability (s)	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
0	0.84	19.81	49.94	8.32
30	0.88	20.95	52.87	9.75
90	0.88	20.97	55.30	10.21
180	0.87	20.62	55.41	9.95
240	0.85	20.26	56.67	9.76
270	0.85	20.30	55.85	9.64

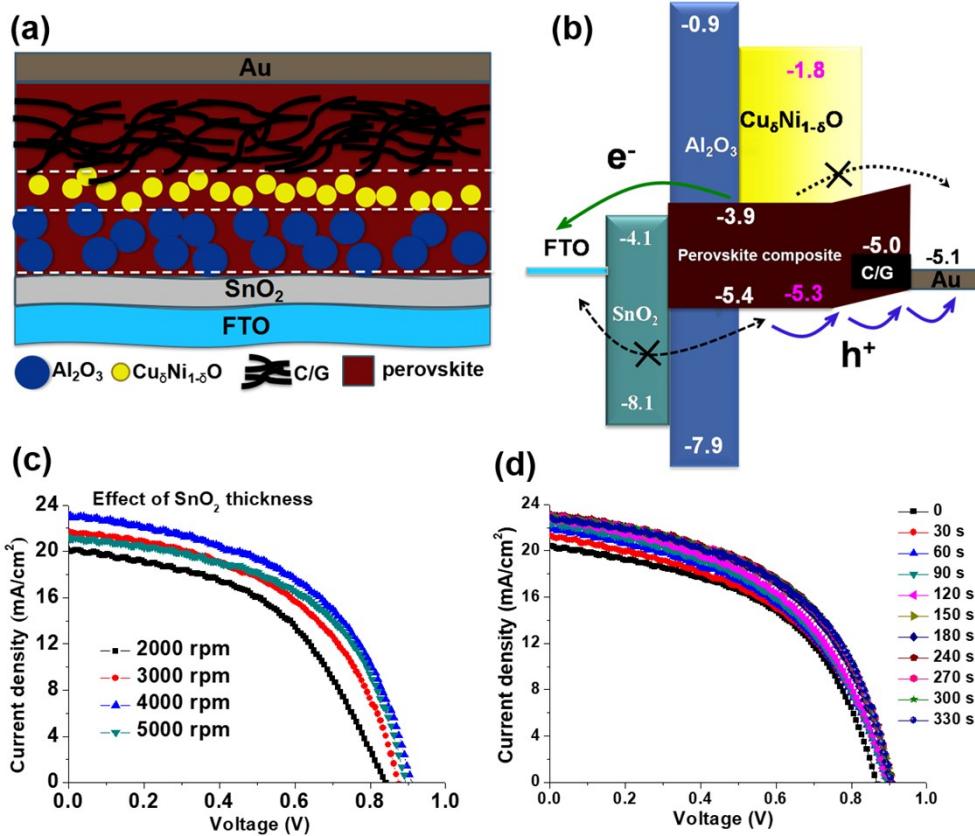


Figure S3 (a) Schematic of device configuration of FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G/MAPbI_{3-x}Cl_x/Au and (b) corresponding the band energy diagram; (c) corresponding J-V performance for different thicknesses of SnO₂ films; (d) continuous 1-sun illumination effect of Carbon and SnO₂ based HCF device for 4000 rpm of SnO₂.

Table S3 Photovoltaic parameters (Figure S3c) of carbon and SnO₂ based HCF-PSCs FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G/MAPbI_{3-x}Cl_x/Au for different rpm of SnO₂.

Spin-coating speed of SnO ₂ precursor	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
2000 rpm	0.84	20.01	47.64	8.01
3000 rpm	0.88	21.57	49.98	9.49
4000 rpm	0.91	23.01	52.12	10.92
5000 rpm	0.90	21.09	53.28	10.12

Table S4 Photovoltaic parameters (Figure S3d) for continuous 1-sun illumination effect of carbon and SnO₂ based HCF device of FTO/(4000 rpm) SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G/MAPbI_{3-x}Cl_x/Au.

Photo stability (s)	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
0	0.87	20.37	50.34	8.89
30	0.90	21.23	47.80	9.14
90	0.90	21.92	47.66	9.41
120	0.89	22.39	47.87	9.54
150	0.90	22.68	48.36	9.88
180	0.91	22.97	49.98	10.45
210	0.91	23.02	50.10	10.50
240	0.91	23.01	52.12	10.92
270	0.91	22.90	51.05	10.64
300	0.91	22.83	51.40	10.68
330	0.91	22.71	51.26	10.60

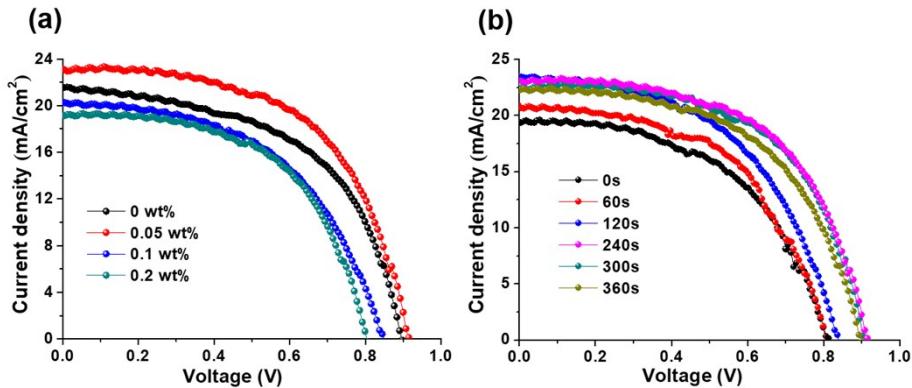


Figure S4 (a) J - V performance for different concentrations of Cu_{0.02}Ni_{0.98}O NPs in C-G-Cu_{0.02}Ni_{0.98}O composite films. (b) J - V performance for the continuous 1-sun illumination effect of C-G-Cu_{0.02}Ni_{0.98}O composites and SnO₂ based HCF device of FTO/c-SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au.

Table S5 Photovoltaic parameters (Figure S4a) for different concentrations of Cu_{0.02}Ni_{0.98}O NPs in C-G-Cu_{0.02}Ni_{0.98}O composite based HCF-PSCs of FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au.

Contents of Cu _{0.02} Ni _{0.98} O	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
w/o Cu _{0.02} Ni _{0.98} O	0.90	21.47	56.22	10.87
0.05 wt% Cu _{0.02} Ni _{0.98} O	0.92	22.97	56.23	11.88
0.1 wt% Cu _{0.02} Ni _{0.98} O	0.85	20.26	54.70	9.42
0.2 wt% Cu _{0.02} Ni _{0.98} O	0.81	19.13	52.13	8.07

Table S6 Photovoltaic parameters (Figure S4b) for continuous 1-sun illumination effect of 0.05 wt% Cu_{0.02}Ni_{0.98}O NPs in C-G-Cu_δNi_{1-δ}O composite based HCF device of FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au.

Photo stability (s)	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
0	0.82	19.38	52.43	8.33
60	0.81	20.69	54.20	9.08
120	0.83	23.26	54.70	10.56
240	0.92	22.97	56.23	11.88
300	0.90	22.52	57.91	11.74
360	0.91	22.21	57.26	11.58

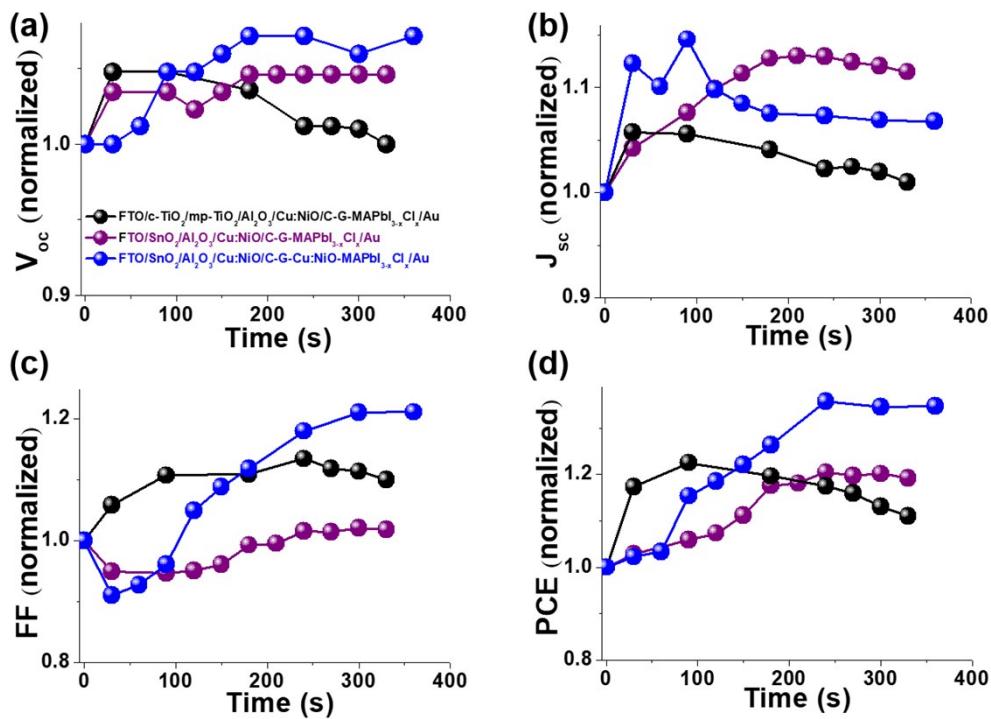


Figure S5 Light soaking effects of three types HCF devices under continuous 1-sun illumination: FTO/c-TiO₂/mp-TiO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-MAPbI_{3-x}Cl_x/Au (black), FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-MAPbI_{3-x}Cl_x/Au (purple) and FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au (blue).

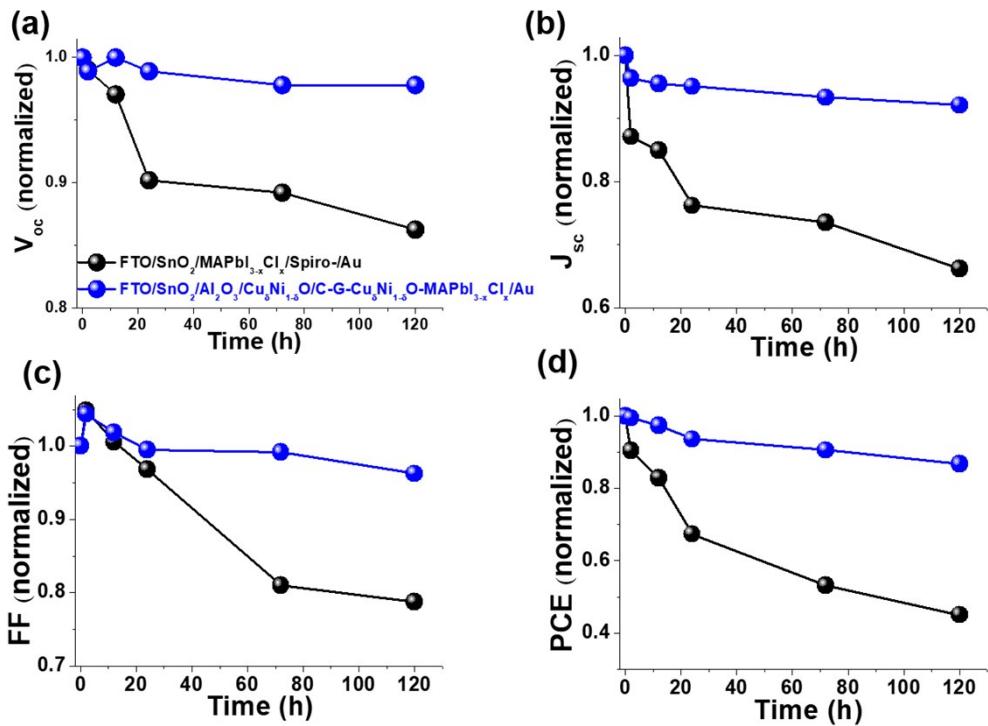


Figure S6 Thermal- and Air-stability for two devices of FTO/SnO₂/MAPbI_{3-x}Cl_x/Spiro-/Au (black) and FTO/SnO₂/Al₂O₃/Cu_δNi_{1-δ}O/C-G-Cu_δNi_{1-δ}O-MAPbI_{3-x}Cl_x/Au (blue) under 85 °C heat treatment and ambient air conditions (humidity 45-50%).

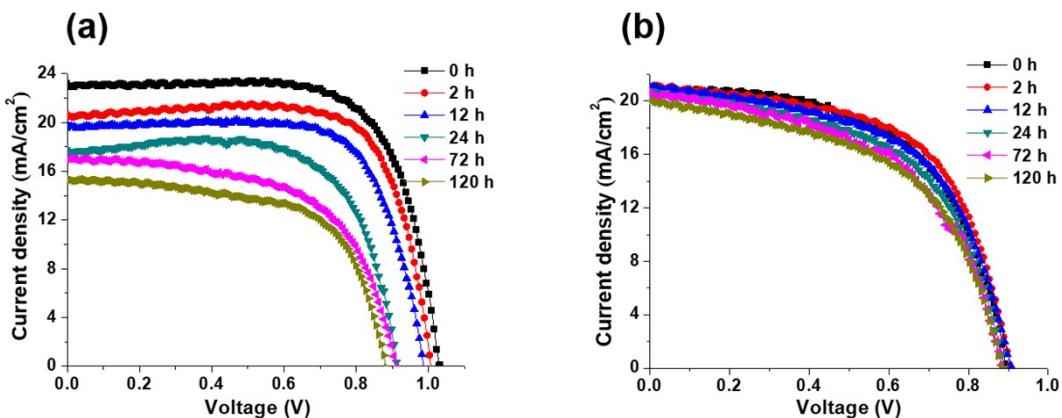


Figure S7 J-V (a) FTO/SnO₂/MAPbI_{3-x}Cl_x/Spiro-OMeTAD/Au, (b) FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au and corresponding J - V performance for thermal-stability at 85 °C in ambient air (45-50 % humidity).

Table S7 Photovoltaic parameters (Figure S6a) of FTO/SnO₂/MAPbI_{3-x}Cl_x/Spiro-OMeTAD/Au for thermal-stability at 85 °C in ambient air (45-50 % humidity).

Thermal stability (h)	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
0	1.03	23.20	75.41	18.02
2	1.02	20.51	75.90	15.88
12	0.99	19.71	72.79	14.21
24	0.92	17.68	70.09	11.54
72	0.91	17.06	58.63	9.11
120	0.88	15.36	57.01	7.71

Table S8 Photovoltaic parameters (Figure S6b) of FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au for thermal-stability at 85 °C in ambient air (45-50 % humidity).

Thermal stability (h)	V _{oc} (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
0	0.91	21.97	56.23	11.24
2	0.90	21.17	58.68	11.18
12	0.91	20.98	57.27	10.94
24	0.90	20.89	55.94	10.52
72	0.89	20.51	55.77	10.18
120	0.89	20.34	55.72	10.09

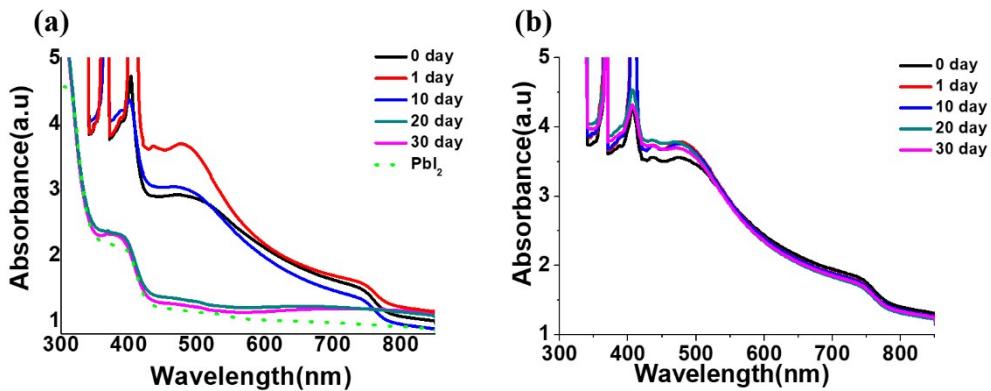


Figure S8 UV performance and thermal-stability for two films (a) FTO/SnO₂/MAPbI_{3-x}Cl_x/Spiro-OMeTAD, (b) FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x at 85 °C heating in ambient air (humidity 45-50 %).

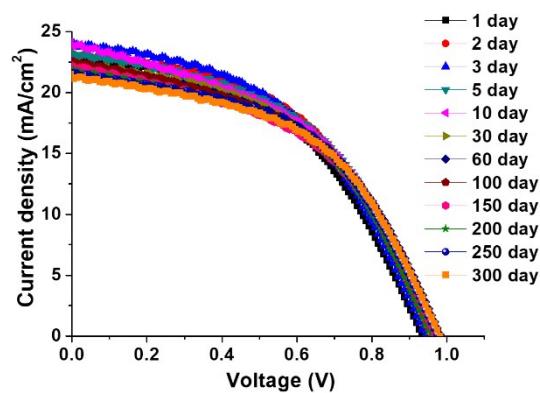


Figure S9 Schematic of device configurations FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au and corresponding *J-V* performance for long-term stability in ambient air (45-50 % humidity).

Table S9 Photovoltaic parameters (Figure S9) of FTO/SnO₂/Al₂O₃/Cu_{0.02}Ni_{0.98}O/C-G-Cu_{0.02}Ni_{0.98}O-MAPbI_{3-x}Cl_x/Au for long-term stability in ambient air (45-50 % humidity).

Long-term stability	Voc (V)	J _{sc} (mA/cm ²)	FF (%)	PCE (%)
1 day	0.951	22.97	55.41	12.11
2 day	0.965	23.88	61.23	14.11
3 day	0.962	24.08	58.10	13.46
5 day	0.966	23.16	57.24	12.81
10 day	0.964	23.83	54.48	12.52
30 day	0.965	22.34	57.20	12.33
60 day	0.961	22.01	57.53	12.12
100 day	0.963	22.58	55.70	12.12
150 day	0.965	22.12	56.37	12.03
200 day	0.951	21.91	56.44	11.76
250 day	0.962	21.66	56.40	11.75
300 day	0.951	21.18	56.62	11.40